

## Features

- High speed switching
- Essentially no switching losses
- Reduction of heat sink requirements
- Higher Frequency Applicability
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information) (Note2)

## Maximum Ratings

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance Junction to Ambient,Max<sup>(Note 3)</sup>: 62°C/W
- Thermal Resistance Junction to Case,Typ : 0.41°C/W

## Applications

- Solar Inverter
- EV Charging Station
- UPS
- Industrial Power Supply

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	1200	V
Gate-Source Voltage (Note 4)	V <sub>GSm</sub>	-8/+22	V
Recommended Gate-Source Voltage	V <sub>GSop</sub>	-4/+18	V
Continuous Drain Current V <sub>GS</sub> =18V	I <sub>D</sub>	80	A
		55	
Pulsed Drain Current (Note 5)	I <sub>DM</sub>	178	A
Avalanche energy,Single pulse (Note 6)	E <sub>AS</sub>	1.1	J
Total Power Dissipation	P <sub>D</sub>	365	W
		182	

Note1:Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Note2:High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.

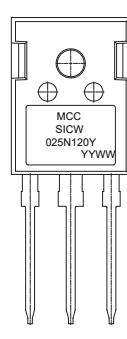
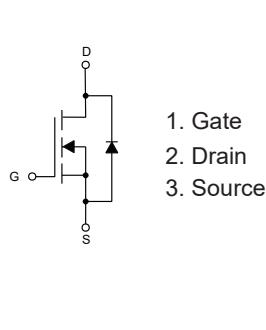
Note3:Device in a still air environment with TA=25°C.

Note4:AC f > 1Hz, duty cycle < 1%

Note5:Pulse Test: Pulse Width Limited by Tjmax.

Note6:V<sub>DD</sub>=75V,L=30mH

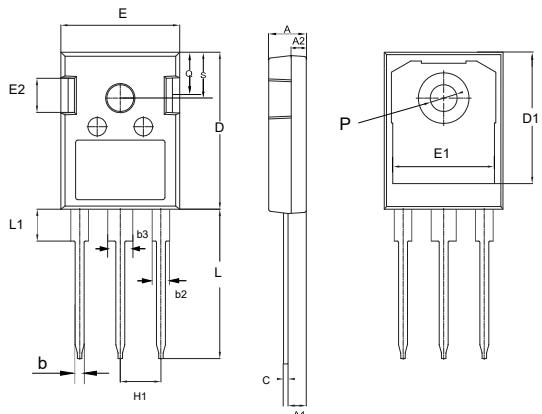
## Internal Structure and Marking Code



Device Code: SICW025N120Y  
Date Code: YYWW (Year & Week)

# SiC N-CHANNEL MOSFET

## TO-247AB



DIM	INCHES		mm		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.090	0.100	2.29	2.54	
A2	0.075	0.083	1.90	2.10	
b	0.043	0.051	1.10	1.30	
b2	0.075	0.087	1.91	2.20	
b3	0.115	0.126	2.92	3.20	
C	0.020	0.028	0.50	0.70	
D	0.819	0.840	20.80	21.34	
D1	0.686	0.702	17.43	17.83	
E	0.620	0.635	15.75	16.13	
E1	0.514	0.530	13.06	13.46	
E2	0.170	0.190	4.32	4.83	
H1	0.215		5.45		TYP
L	0.781	0.797	19.85	20.25	
L1	0.159	0.177	4.05	4.49	
P	0.140	0.144	3.55	3.65	Φ
Q	0.220	0.244	5.59	6.19	
S	0.242		6.15		TYP

**Electrical Characteristics @  $T_j=25^\circ\text{C}$  (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS}=0\text{V}, I_D=100\mu\text{A}$	1200			V
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=18\text{V}$		10	100	nA
Gate-Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=15\text{mA}$	2.0	2.7	4.0	V
		$V_{DS}=V_{GS}, I_D=15\text{mA}, T_j=175^\circ\text{C}$		2.0		
Drain-Source On-Resistance	$R_{DS(\text{on})}$	$V_{GS}=18\text{V}, I_D=40\text{A}$		25	40	$\text{m}\Omega$
		$V_{GS}=18\text{V}, I_D=40\text{A}, T_j=175^\circ\text{C}$		46		$\text{m}\Omega$
Transconductance	$g_{FS}$	$V_{DS}=20\text{V}, I_D=40\text{A}$		28		S
		$V_{DS}=20\text{V}, I_D=40\text{A}, T_j=175^\circ\text{C}$		26		
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=800\text{V}, V_{GS}=0\text{V}, f=100\text{kHz}$ $V_{AC}=25\text{mV}$		4710		pF
Output Capacitance	$C_{oss}$			160		
Reverse Transfer Capacitance	$C_{rss}$			6.8		
Cross Stored Energy	$E_{oss}$			84		$\mu\text{J}$
Total Gate Charge	$Q_g$	$V_{DS}=800\text{V}, V_{GS}=-4/+18\text{V}, I_D=40\text{A}$		152		nC
Gate-Source Charge	$Q_{gs}$			40		
Gate-Drain Charge	$Q_{gd}$			61		
Internal Gate Resistance	$R_g$	$f=1\text{MHz}$		2		$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=800\text{V}, V_{GS}=-4/+18\text{V},$ $R_G=2.4\Omega, I_D=40\text{A}, L=100\mu\text{H}$		19		ns
Turn-On Rise Time	$t_r$			37.5		
Turn-Off Delay Time	$t_{d(off)}$			25		
Turn-Off Fall Time	$t_f$			14		
Turn-On switching energy	$E_{on}$			580		$\mu\text{J}$
Turn-Off switching energy	$E_{off}$			249		
<b>Diode Characteristics</b>						
Maximum Continuous Diode Forward Current	$I_S$			70		A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=-4\text{V}, I_{SD}=20\text{A}$		4.8		V
		$V_{GS}=0\text{V}, I_{SD}=20\text{A}, T_j=175^\circ\text{C}$		3.0		V
Reverse Recovery Time	$t_{rr}$	$I_{SD}=40\text{A}, V_R=800\text{V},$ $V_{GS}=-4\text{V}$ $dI_F/dt=2500\text{A}/\mu\text{s}$		48		ns
Reverse Recovery Charge	$Q_{rr}$			323		nC
Peak reverse recovery current	$I_{rrm}$			11		A

## Curve Characteristics ( $T_j=25^\circ\text{C}$ unless otherwise specified)

Fig. 1 - Typical Output Characteristic

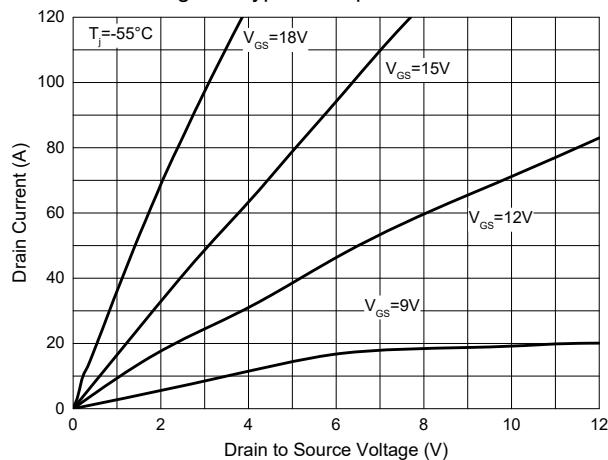


Fig. 2 - Typical Output Characteristic

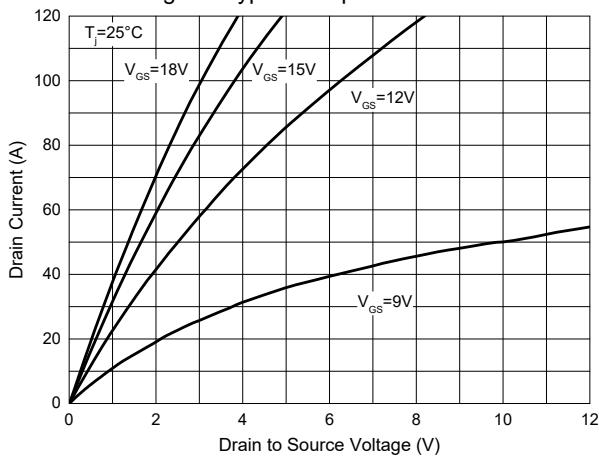


Fig. 3 - Typical Output Characteristic

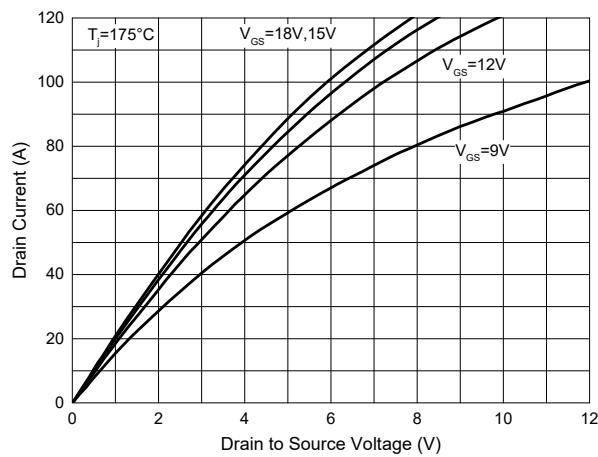


Fig. 4 - Typical Transfer Characteristic

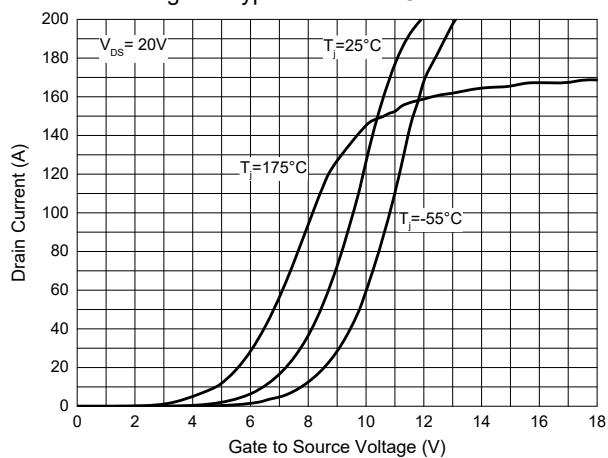


Fig. 5 On-Resistance vs Temperature

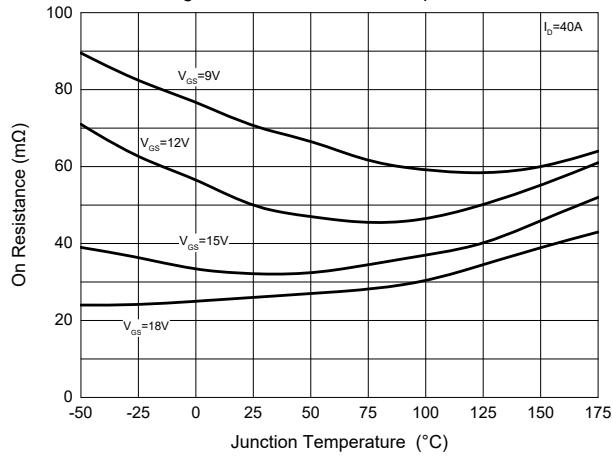
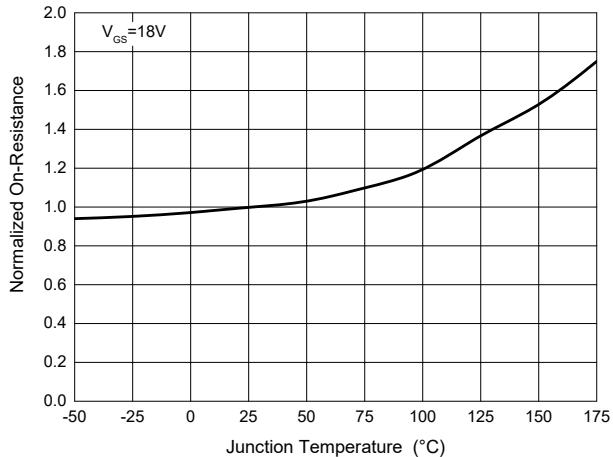


Fig. 6 - Normalized On-Resistance vs Temperature



## Curve Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise specified)

Fig. 7 - On-Resistance vs. Drain Current

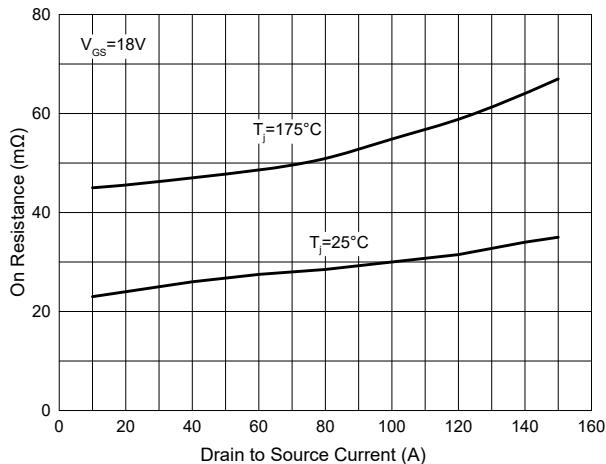


Fig. 8 - Reverse Output Voltage

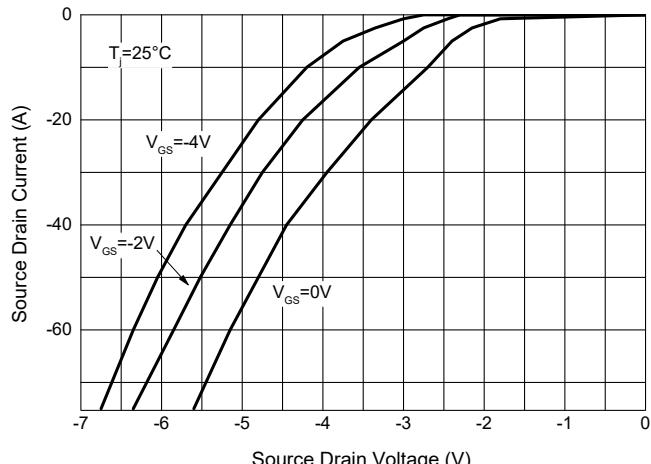


Fig. 9 - Reverse Output Voltage

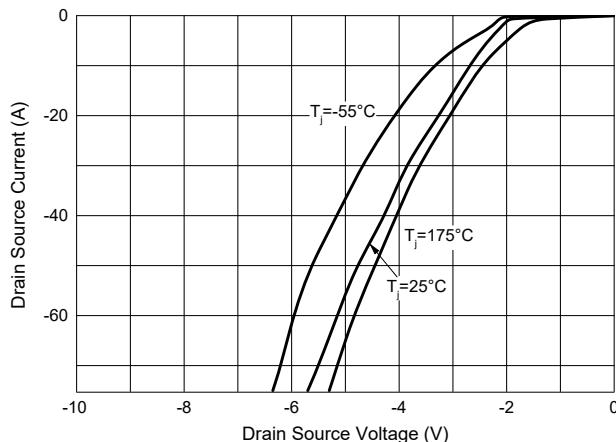


Fig. 10 - 3<sup>rd</sup> Quadrant Characteristic

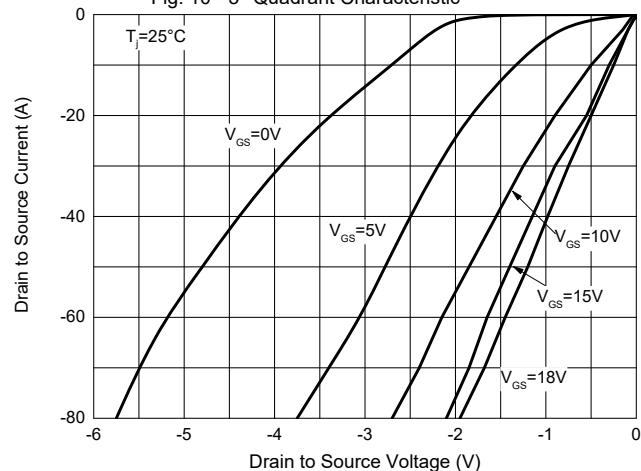


Fig. 11 - Threshold Voltage vs Temperature

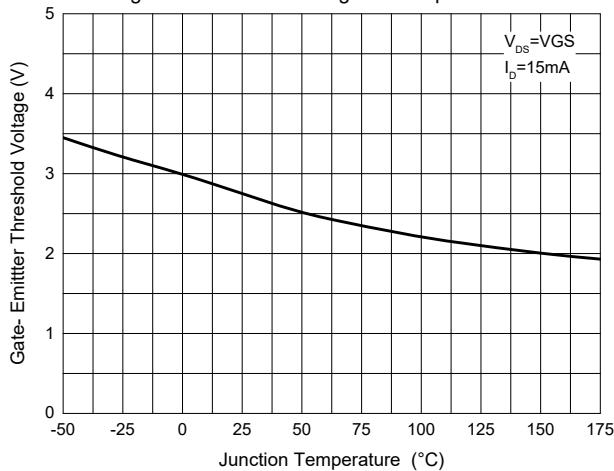
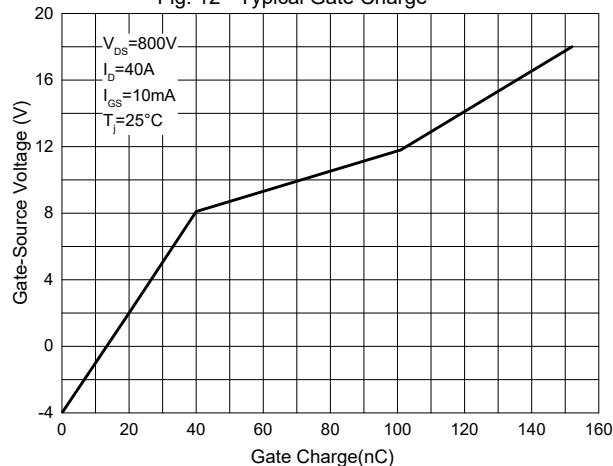
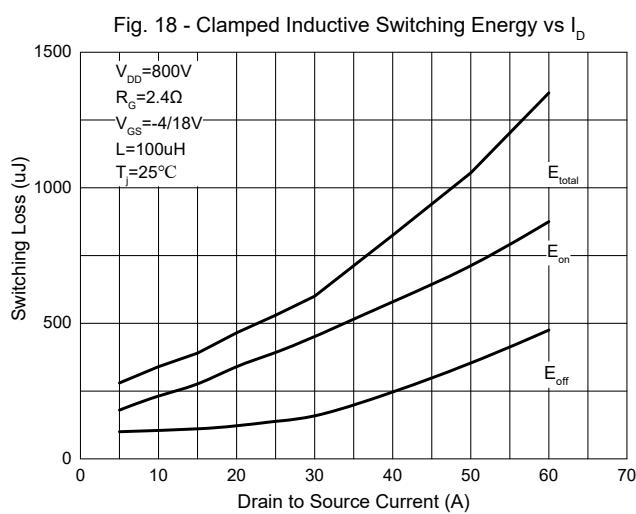
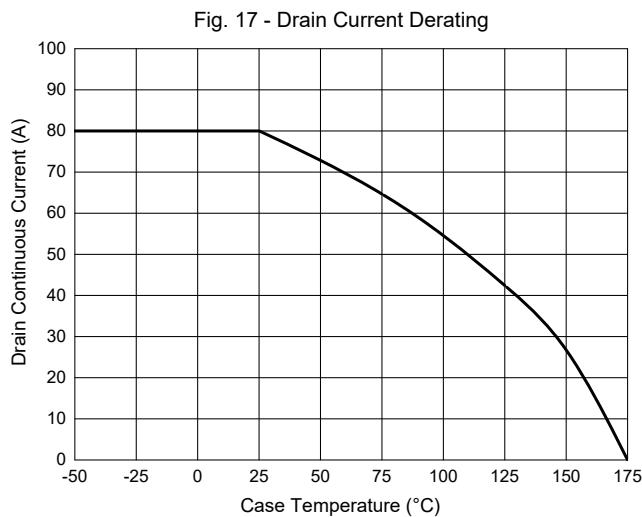
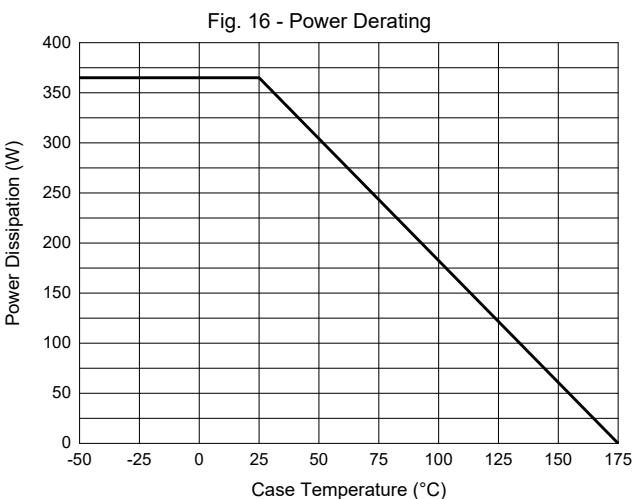
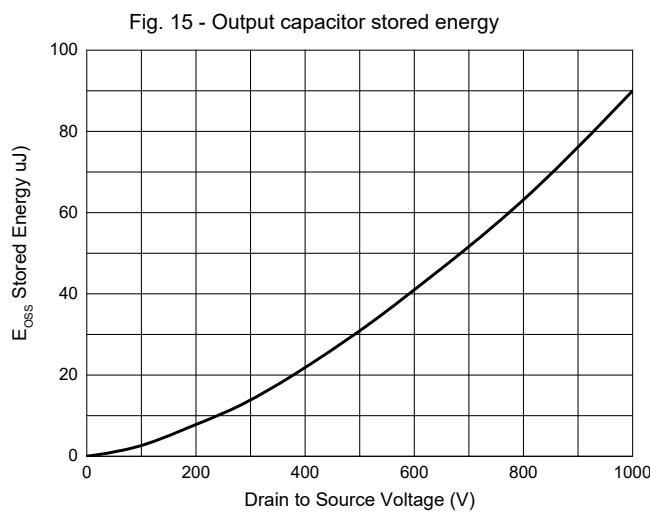
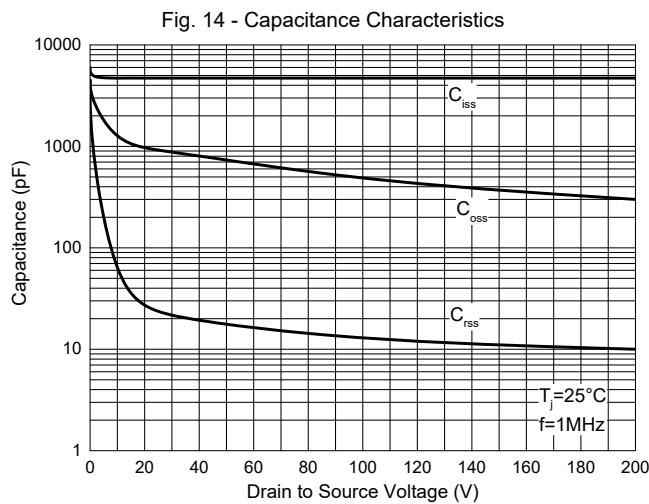
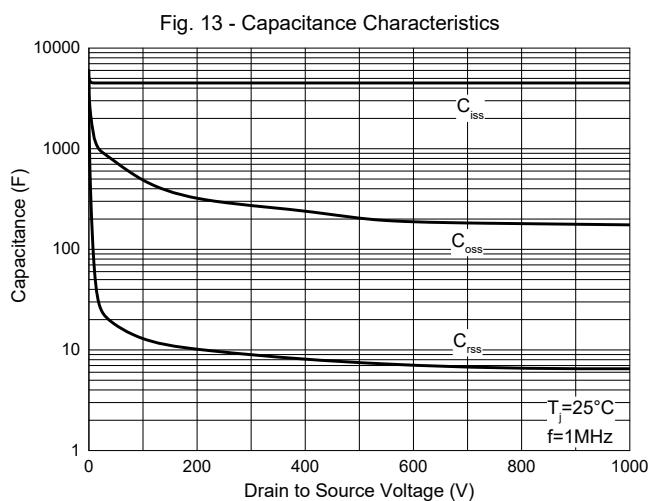


Fig. 12 - Typical Gate Charge



**Curve Characteristics** ( $T_j=25^\circ\text{C}$  unless otherwise specified)



## Curve Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise specified)

Fig. 19 - Switch Loss VS  $R_G$

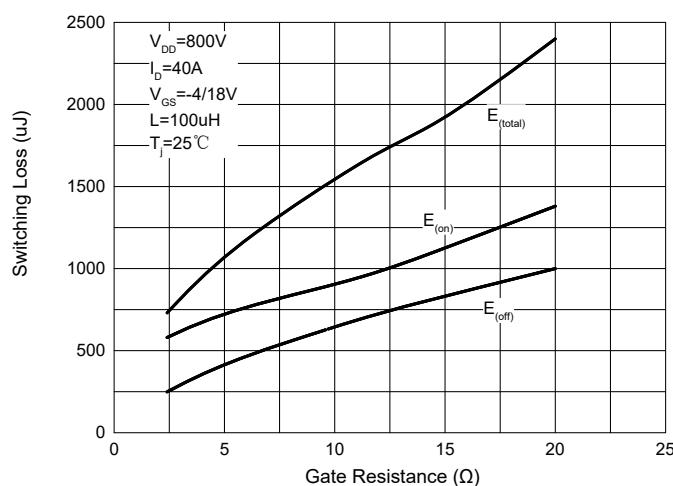


Fig. 21- Safe Operation Area

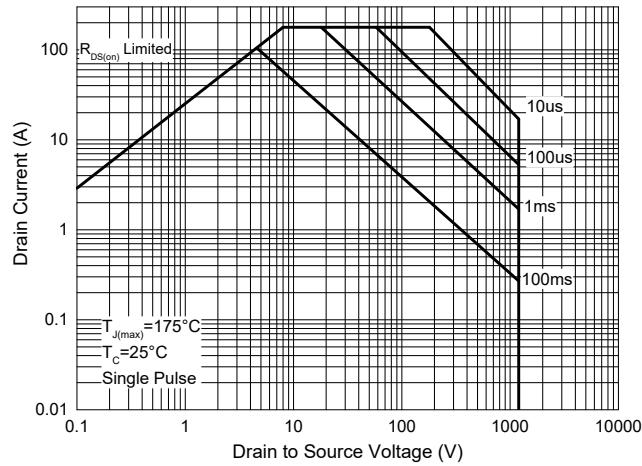


Fig. 20 - Switching Times vs Gate Resistance

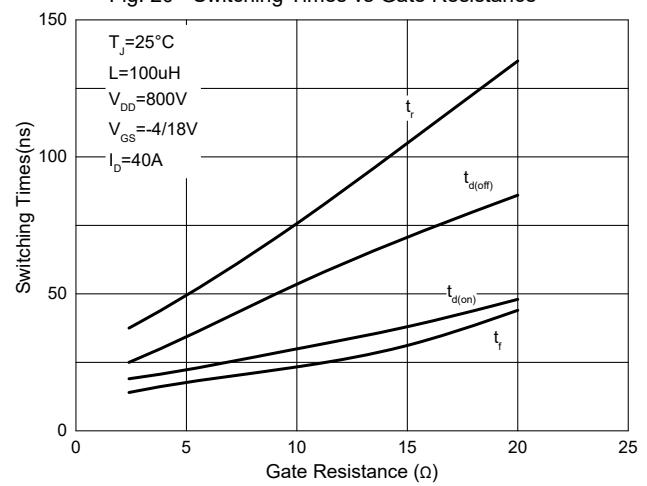
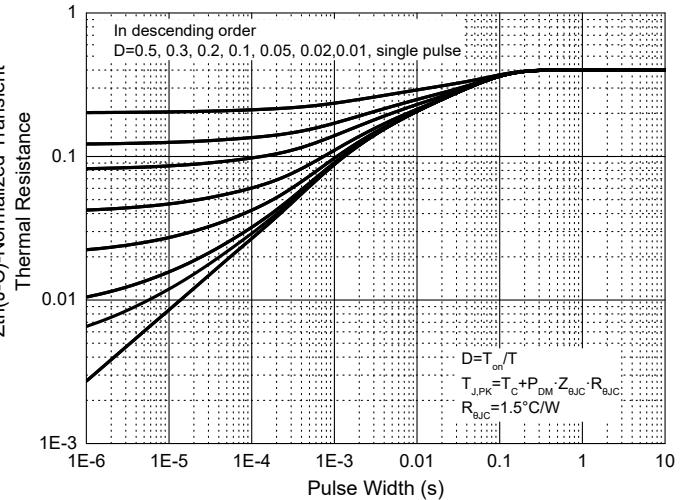


Fig. 22- Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
Part Number-BP	Tube:30pcs/Tube, 1.8K/Ctn;

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